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# Synthesis, optical and dielectric studies on novel semi organic nonlinear optical crystal by solution growth technique

# V. Chithambaram<sup>a</sup>, S. Jerome Das<sup>b</sup>, S. Krishnan<sup>c,\*</sup>

<sup>a</sup> Department of Physics, AMET University, Kanathur, Chennai 603112, India

<sup>b</sup> Department of Physics, Loyola College, Chennai 600 034, India

<sup>c</sup> Department of Physics, R. M. K. Engineering College, Kavaraipettai 601206, Chennai, India

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# **1. Introduction**

In recent years, second order nonlinear optical materials have attracted many researchers because of their potential applications in various emerging technological fields [\[1–7\]. T](#page-2-0)oday, crystal growth technology has advanced rapidly for the development of novel nonlinear optical materials (NLO) for various applications such as optical switching, frequency conversion and electro-optical modulation [\[8–13\]. T](#page-3-0)he organic NLO materials have large nonlinear optical coefficients compared to inorganic material, but their use is impeded by their poor mechanical and thermal properties and low laser damage threshold [\[14\]. T](#page-3-0)he inorganic NLO materials have excellent mechanical and thermal properties but possess relatively modest optical nonlinearities due to lack of extended  $\pi$ -electron delocalization [\[15\]. I](#page-3-0)n view of these problems, a new class of materials has been developed from organic and inorganic complexes called semi organic [\[14,16\]. I](#page-3-0)n thesematerials, high optical nonlinearity of pure organic compound is combined with the favorable mechanical and thermal properties of inorganic materials [\[14–18\]. S](#page-3-0)emi organic crystals have large damage threshold, wide transparency range, less deliquescence, excellent nonlinear optical coefficient, low angular sensitivity and exceptional mechanical properties [\[19–22\].](#page-3-0)

# ABSTRACT

Bisthiourea lead acetate Pb[SC(NH<sub>2</sub>)<sub>2</sub>]<sub>2</sub>(CH<sub>3</sub>COO)<sub>2</sub>), a novel semi organic non linear optical crystal having dimensions 17 mm  $\times$  2 mm  $\times$  2 mm were grown using slow evaporation technique. The lattice parameters for the grown crystals were determined using single crystal XRD. The presence of functional groups for the grown crystals was confirmed using Fourier transform infrared (FT-IR) spectroscopy. The optical absorption studies show that the material has wide optical transparency in the entire visible region. The dielectric constant and dielectric loss has been studied as a function of frequency for various temperatures and the results were discussed in detail. The second harmonic generation was confirmed by Kurtz powder method and it is found to be 5 times than that of potassium dihydrogen phosphate (KDP) crystal.

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In the present work, bisthiourea lead acetate (BTLA), a desirable semi organic nonlinear optical crystal, has been grown from aqueous solution using slow evaporation technique. The grown crystals were subjected to various characterizations such as single crystal X-ray diffraction analysis, Fourier transform infrared (FTIR) analysis, optical absorption studies, dielectric studies and nonlinear optical studies and were discussed in detail.

#### **2. Experimental**

#### 2.1. Materials

(AR grade) thiourea and lead acetate purchased from Merck were used to synthesis the crystal. Triple distilled water was used as solvent.

#### 2.2. Crystal growth

Single crystals of BTLA were grown by dissolving (AR grade) thiourea and lead acetate in the ratio 2:1 using triple distilled water. The chemical reaction is as follows.

 $(CS(NH_2)_2)_2 + Pb(CH_3COO)_2 \rightarrow Pb[SC(NH_2)_2]_2(CH_3COO)_2)$ 

Extreme care was taken to minimize the thermal and mechanical disturbances to the supersaturated solution. After recrystallisation and filtration, optically good quality and needle shaped crystal having dimensions  $17 \text{ mm} \times 2 \text{ mm} \times 2 \text{ mm}$  was obtained within a period of 6 weeks. The photograph of the grown crystal is shown in the [Fig. 1.](#page-1-0)

<sup>∗</sup> Corresponding author. Tel.: +91 44 27925102; fax: +91 44 27925193. E-mail address: [skrishnanjp@gmail.com](mailto:skrishnanjp@gmail.com) (S. Krishnan).

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**Fig. 1.** Photograph of as grown crystal of BTLA.

## **3. Results and discussion**

#### 3.1. Single crystal X-ray diffraction

The grown crystals were subjected to single crystal X-ray diffraction analysis using ENRAF NONIUS CAD4 X-ray diffractometer to determine the cell parameters and it reveals that the BTLA crystal crystallizes in monoclinic system having non-centrosymmetric space group  $P_{21}$ . The lattice parameters were found to be  $a = 4.567(3)$ Å,  $b = 15.827(7)$ Å,  $c = 13.744(5)$ Å,  $\beta$  = 92.44(4) $\circ$  and V = 992.53 Å<sup>3</sup>.

### 3.2. FTIR analysis

The FTIR spectrum of the grown crystals was recorded in the range 400–4000 cm−<sup>1</sup> using IFS BRUKKER 66 V spectrophotometer and the resultant spectrum is shown in the Fig. 2. The symmetric and asymmetric  $C = S$  stretching vibrations of thiourea are observed at 719 cm<sup>-1</sup>. The COH stretching mode occurred at 1046 cm<sup>-1</sup> in the spectrum. The absorption band at  $1532 \text{ cm}^{-1}$  is due to  $NH<sub>2</sub>$  in group deformation. The C=H valence and C=H valence of thiourea are observed at 3191 cm−<sup>1</sup> and 3304 cm−<sup>1</sup> respectively. The C=H symmetrical band is assigned at 3373 cm<sup>-1</sup> in the spectrum. The symmetric NH<sub>2</sub> stretching is assigned at 3304 cm<sup>-1</sup>. The absorption band at 1630 cm<sup>-1</sup> shows the functional group NH<sub>2</sub> in bending mode. The absorption band at 1409 cm<sup>-1</sup> can be



**Fig. 2.** FT-IR spectrum of BTLA crystal.

|--|

Comparison of IR bands of BTLA with thiourea.



assigned to  $C = S$  stretching vibration. The sharp and intense peak at 670 and 719 cm−<sup>1</sup> attributed to double bond character of the  $C = S$  band on coordination. The band at lower frequency 550 cm<sup>-1</sup> is attributed to asymmetric N–C–N bending vibration. The symmetric and asymmetric stretching of COO− is found to be at 1409 and 1532 cm<sup>-1</sup> respectively. The symmetrical CH<sub>3</sub> bending can be assigned at 1333 cm−1. The symmetrical C–C stretching is found to be at 925 cm<sup>-1</sup>. The OCO bending is found to be at  $670 \text{ cm}^{-1}$ . The characteristic vibrational frequencies of the functional groups of BTLA have been compared with pure thiourea [\[23,24\]. T](#page-3-0)his confirms the presence of metal acetate in the crystal lattice of thiourea. The comparison of characteristic vibrational frequencies has been tabulated in Table 1.

### 3.3. Optical absorption studies

The optical absorption spectrum for the grown crystals was recorded in the range 200–2000 nm using VARIAN CARY 5E SEC-TROPHOTOMETER and is shown in the Fig. 3. The resultant spectrum shows that the crystal has very low absorbance in the entire visible and IR region. The UV cut-off wavelength is found to be at 320 nm. This very low absorption property of the grown crystal in the entire visible region suggests its suitability for second harmonic generation [\[25,26\].](#page-3-0)

The optical absorption coefficient  $(\alpha)$  was calculated from the transmittance using the following relation,

$$
\alpha = \frac{1}{t} \log \left( \frac{1}{T} \right) \tag{1}
$$

where  $T$  is the transmittance and  $t$  is the thickness of the crystal.

As a direct band gap, the crystal under study has an absorption coefficient  $(\alpha)$  obeying the following relation for high photon

5  $\overline{4}$ Abs (Å) 3  $\mathfrak{p}$ 200 600 800 1000 1200 1400 1600 1800 2000 2200  $\Omega$ 400 Wavelength (nm)

**Fig. 3.** Optical absorption spectrum of the BTLA crystal.

<span id="page-2-0"></span>



energies  $(h\nu)$ :

$$
\alpha = \frac{A(h\nu - E_g)^{1/2}}{h\nu} \tag{2}
$$

where  $E_g$  is the optical band gap of the crystal and A is a constant. The plot of variation of  $(\alpha h \nu)^2$  versus hv is shown in Fig. 4.  $E_{\sigma}$  is evaluated using extrapolation of the linear part [\[27\].](#page-3-0) The energy absorption gap is of direct type and the band gap energy is found to be 3.3 eV. As a consequence of a wide band gap, the grown crystal has a large transmittance in the visible region [\[28\].](#page-3-0)

#### 3.4. Dielectric studies

An optically good quality single crystal of BTLA was selected for dielectric measurements using HIOKI 3532-50 LCR HITESTER. The selected samples were cut using a diamond saw and polished using paraffin oil. Silver paint was applied on the both faces to make a capacitor with the crystal as a dielectric material. The dielectric constant is calculated using the relation

$$
\varepsilon' = \frac{Cd}{\varepsilon_0 A} \tag{3}
$$

where C is the capacitance, d is the thickness, A is the area and  $\varepsilon_0$ is the absolute permittivity of the free space (8.854  $\times$  10<sup>-12</sup> F/m). The variation of dielectric constant ( $\varepsilon'$ ) was studied as a function of frequency for the grown crystal at various temperatures viz., 308, 323, and 338 K and is shown in Fig. 5. The high value of dielectric constant at low frequencies may be due to the presence of all the four polarizations and its low value at higher frequencies may be due to the loss of significance of these polarizations gradually [\[29\].](#page-3-0) From the plot, it is also observed that dielectric constant decreases with increase in frequency. The variation of dielectric loss with frequency is shown in Fig. 6. The characteristics of low dielectric loss at very high frequency suggest that it possesses enhanced opti-



**Fig. 5.** Variation of dielectric constant vs. log f.



Fig. 6. Variation of dielectric loss vs. log f.

cal quality with lesser defects and this parameter is essential for nonlinear optical applications [\[30\].](#page-3-0)

#### 3.5. Kurtz powder SHG test

The second harmonic generation efficiency measurement was carried out on the grown crystal using the Kurtz–Perry powder technique. The crystal was grounded into a homogenous powder of particles and densely packed between two transparent glass slides. The powder sample with average particle size  $100-115$   $\mu$  were illuminated using Q-switched Nd: YAG laser emitting a fundamental wavelength of 1064 nm with the pulse width of 8 ns. The second harmonic generations was confirmed by the emission of green radiation (532 nm). The output power is found to be 5 times than that of KDP.

# **4. Conclusions**

Optically transparent single crystals of BTLA were grown from aqueous solution using slow evaporation technique. Single crystal X-ray diffraction analysis confirms that the grown crystals crystallize in monoclinic system having space group  $P_{21}$ . FTIR analysis confirms the presence of lead acetate in the crystal lattice of thiourea. The UV cut-off wavelength is found to be at 320 nm and the band gap energy is found to be 3.3 eV. Dielectric constant decreases with increase in frequency and very low values of dielectric loss infer very high purity of the crystal. NLO studies confirm that the SHG efficiency of BTLA is 5 times than that of KDP crystal. All these studies indicate that the BTLA crystal can be considered as a potential candidate for the fabrication of optoelectronic devices.

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